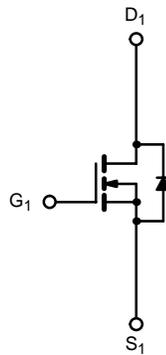
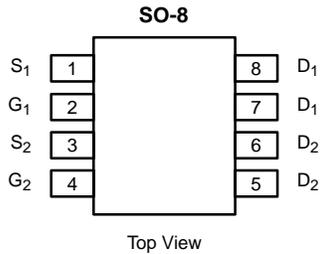


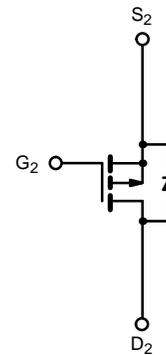


N- and P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
	V_{DS} (V)	$R_{DS(ON)}$ (Ω)	I_D (A)
N-Channel	30	0.065 @ $V_{GS} = 10$ V	± 3.9
		0.095 @ $V_{GS} = 4.5$ V	± 3.1
P-Channel	-30	0.085 @ $V_{GS} = -10$ V	± 3.5
		0.19 @ $V_{GS} = -4.5$ V	± 2.5



N-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
PARAMETER	SYMBOL	N-CHANNEL	P-CHANNEL	UNIT
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 20	± 20	
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^A	$T_A = 25^\circ\text{C}$	± 3.9	± 3.5	A
	$T_A = 70^\circ\text{C}$	± 3.1	± 2.8	
Pulsed Drain Current	I_{DM}	± 20	± 20	
Continuous Source Current (Diode Conduction) ^A	I_S	1.7	-1.7	
Maximum Power Dissipation ^A	$T_A = 25^\circ\text{C}$	2.0		W
	$T_A = 70^\circ\text{C}$	1.3		
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150		$^\circ\text{C}$

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	N- OR P-CHANNEL	UNIT
Maximum Junction-to-Ambient ^A	R_{thJA}	62.5	$^\circ\text{C}/\text{W}$

Notes

A. Surface Mounted on FR4 Board, $t \leq 10$ sec.

Updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #70155. For SPICE model information via the Worldwide Web: <http://www.siliconix.com/www/product/spice.htm>



SPECIFICATIONS (T _J = 25°C UNLESS OTHERWISE NOTED)								
PARAMETER	SYMBOL	TEST CONDITION		MIN	TYP	MAX	UNIT	
STATIC								
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	N-Ch	1.0			V	
		V _{DS} = V _{GS} , I _D = -250 μA	P-Ch	-1.0				
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V	N-Ch			±100	nA	
			P-Ch			±100		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	N-Ch			1	μA	
		V _{DS} = -30 V, V _{GS} = 0 V	P-Ch			-1		
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55°C	N-Ch			25		
		V _{DS} = -30 V, V _{GS} = 0 V, T _J = 55°C	P-Ch			-25		
On-State Drain Current ^B	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	N-Ch	15			A	
		V _{DS} ≥ -5 V, V _{GS} = -10 V	P-Ch	-15				
Drain-Source On-State Resistance ^B	r _{DS(on)}	V _{GS} = 10 V, I _D = 3.9 A	N-Ch		0.043	0.065	Ω	
		V _{GS} = -10 V, I _D = -2.5 A	P-Ch		0.066	0.085		
		V _{GS} = 4.5 V, I _D = 3.1 A	N-Ch		0.075	0.095		
		V _{GS} = -4.5 V, I _D = -1.8 A	P-Ch		0.125	0.19		
Forward Transconductance ^B	g _{fs}	V _{DS} = 15 V, I _D = 3.9 A	N-Ch		7		S	
		V _{DS} = -15 V, I _D = -2.5 A	P-Ch		5			
Diode Forward Voltage ^B	V _{SD}	I _S = 1.7 A, V _{GS} = 0 V	N-Ch		0.8	1.2	V	
		I _S = -1.7 A, V _{GS} = 0 V	P-Ch		-0.8	-1.2		
DYNAMICA								
Total Gate Charge	Q _g	N-Channel V _{DS} = 10 V, V _{GS} = 10 V, I _D = 3.9 A P-Channel V _{DS} = -10 V, V _{GS} = -10 V, I _D = -2.5 A	N-Ch		9.8	15	nC	
Gate-Source Charge	Q _{gs}		N-Ch		2.1			
Gate-Drain Charge	Q _{gd}		N-Ch		1.6			
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 10 V, R _L = 10 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _G = 6 Ω P-Channel V _{DD} = -10 V, R _L = 10 Ω I _D ≅ -1 A, V _{GEN} = -10 V, R _G = 6 Ω	N-Ch		9	15	ns	
Rise Time	t _r		N-Ch		6	18		
Turn-Off Delay Time	t _{d(off)}		N-Ch		18	27		
Fall Time	t _f		N-Ch		6	15		
Source-Drain Reverse Recovery Time	t _{rr}		I _F = 1.7 A, di/dt = 100 A/μs	N-Ch		52		80
			I _F = -1.7 A, di/dt = 100 A/μs	P-Ch		50		80

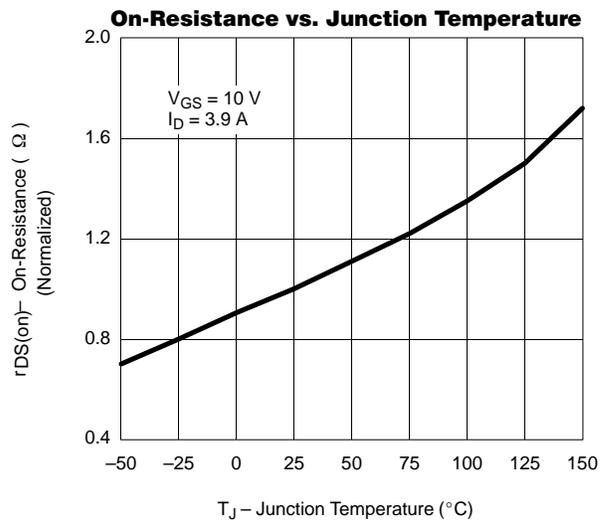
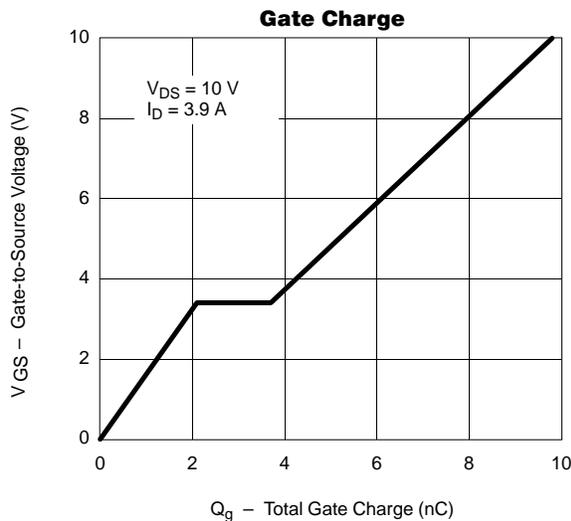
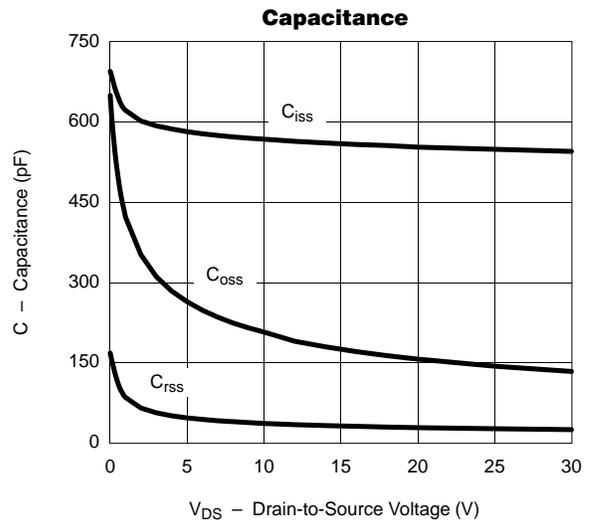
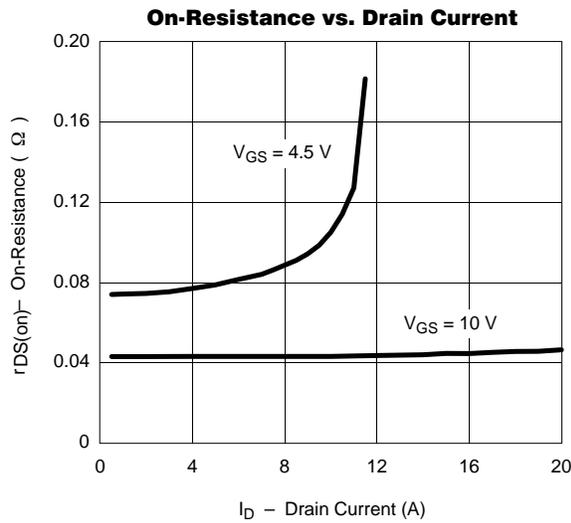
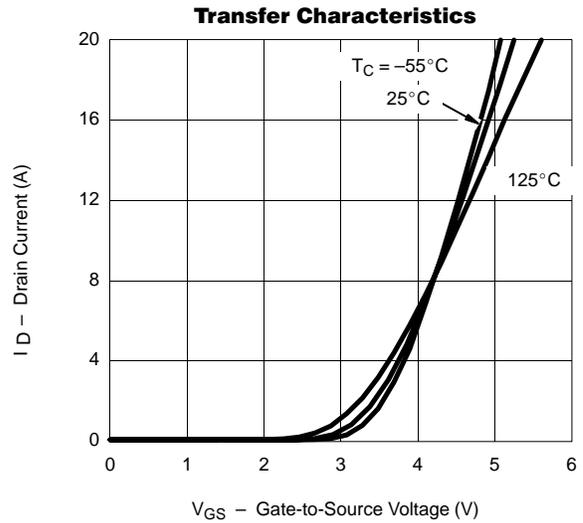
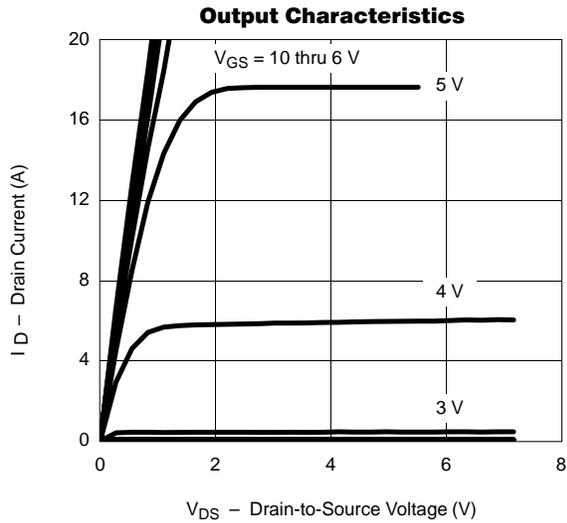
Notes

- A. Guaranteed by design, not subject to production testing.
- B. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.



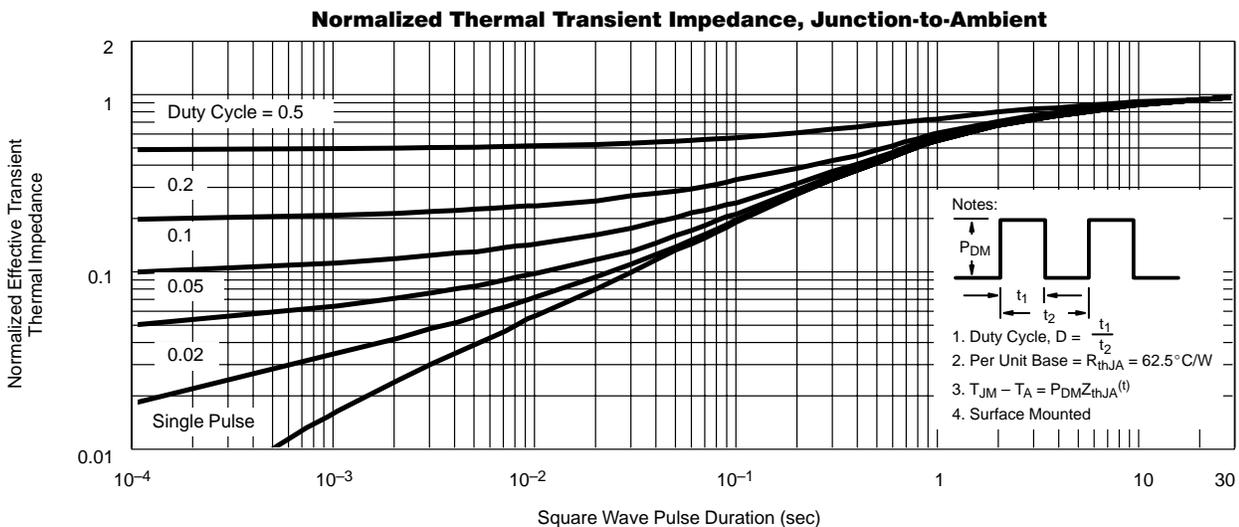
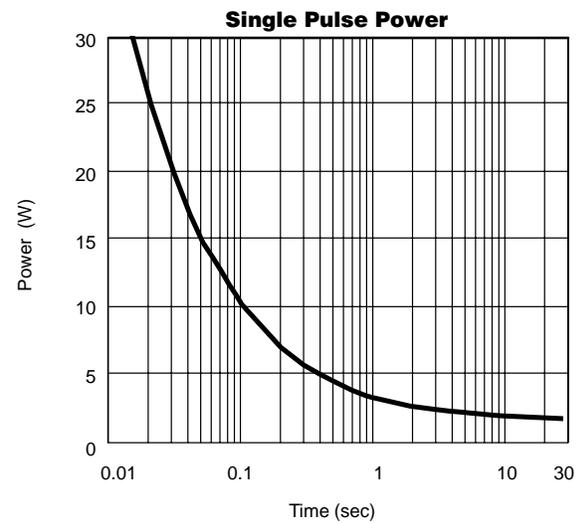
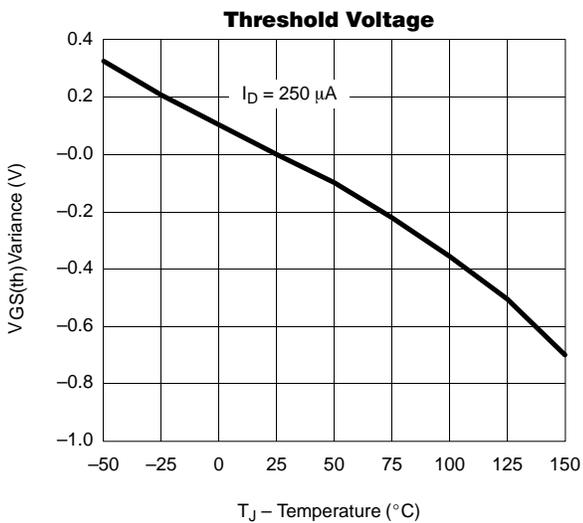
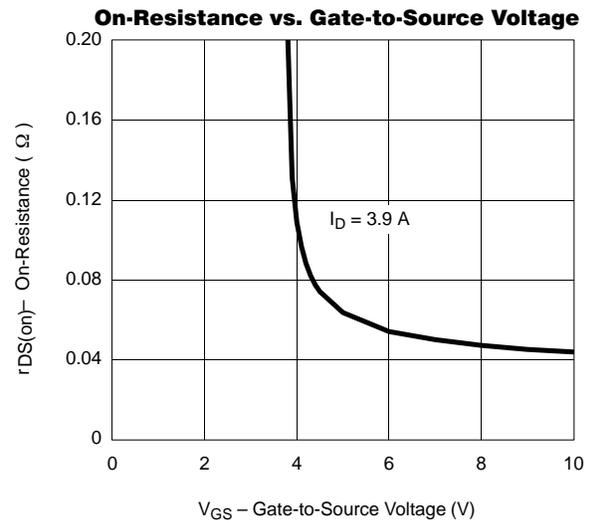
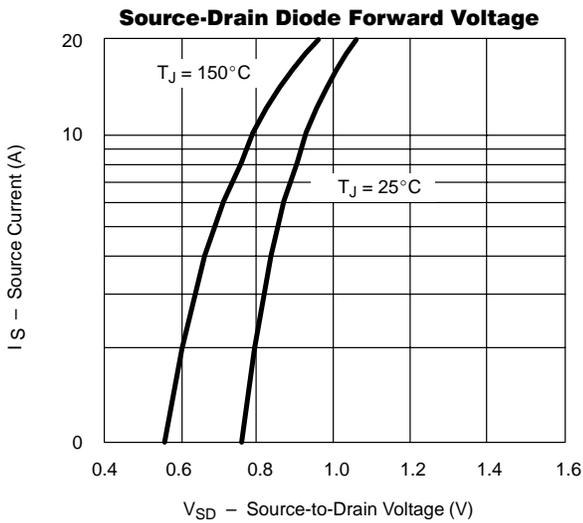
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

N-CHANNEL



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

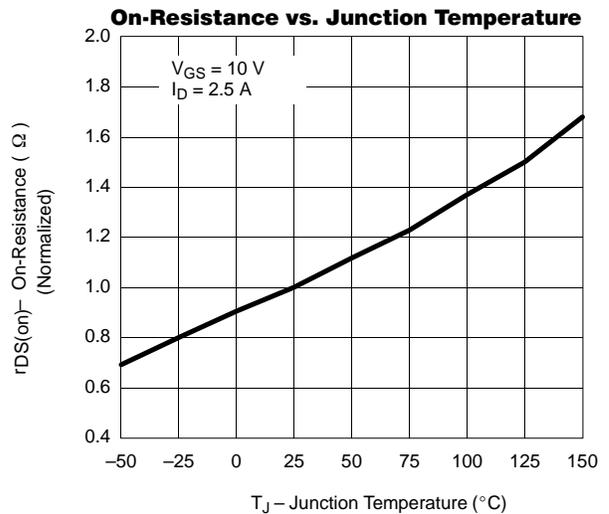
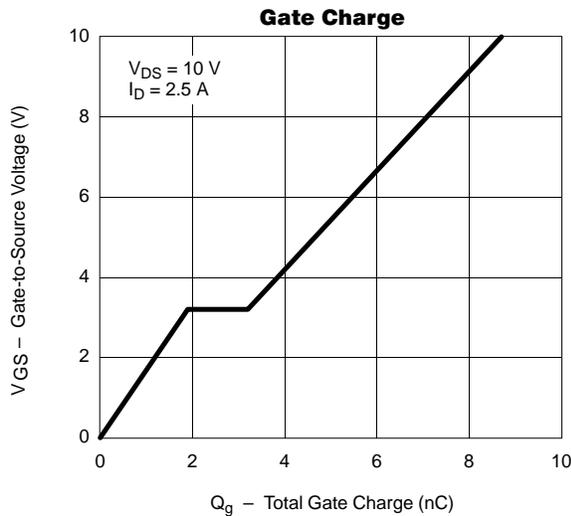
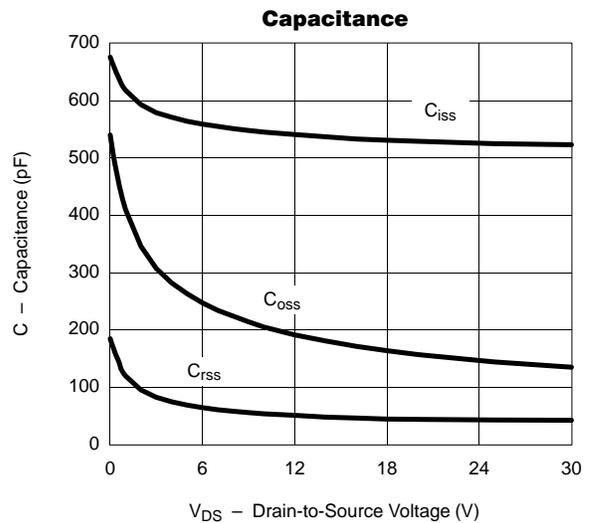
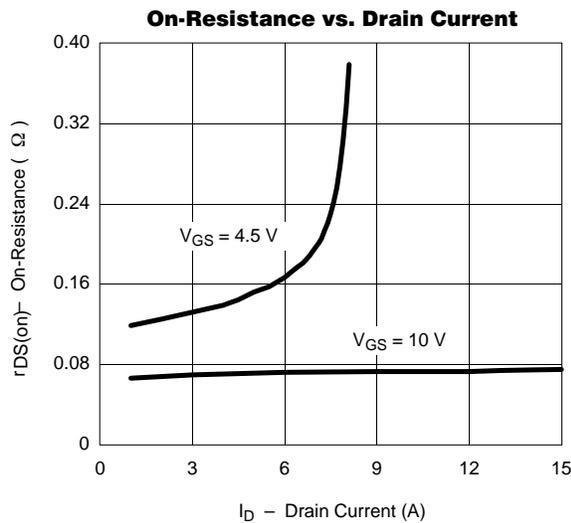
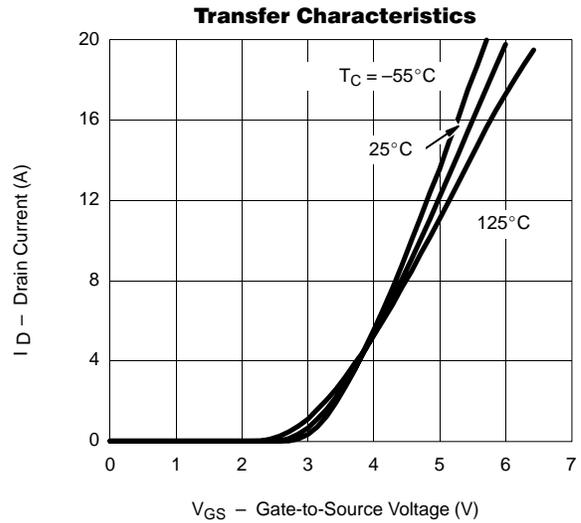
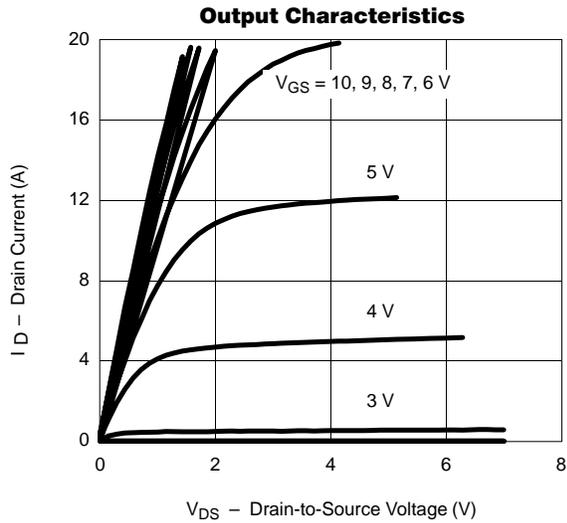
N-CHANNEL





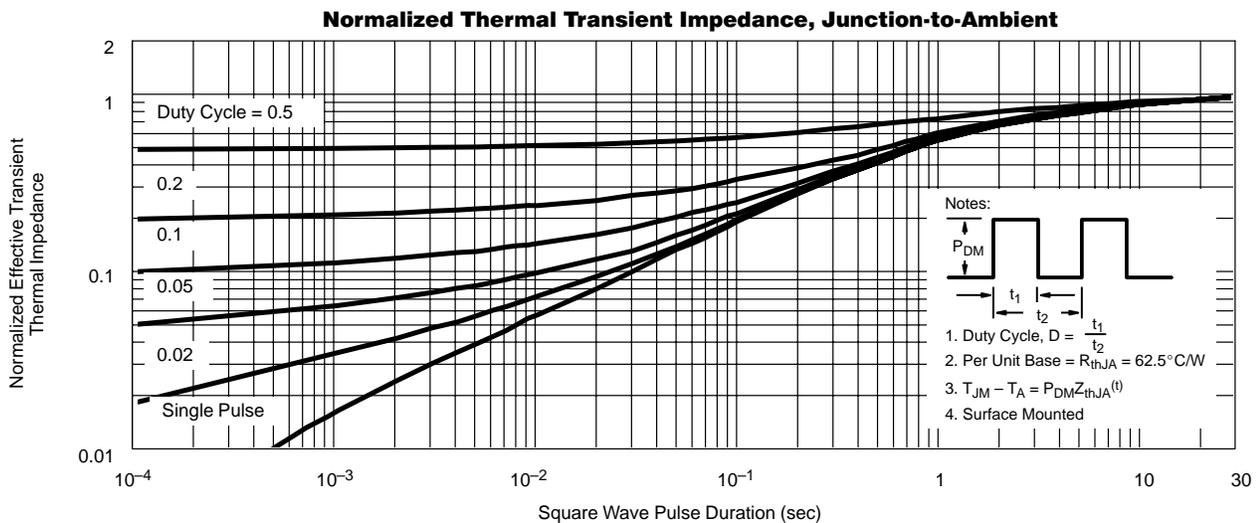
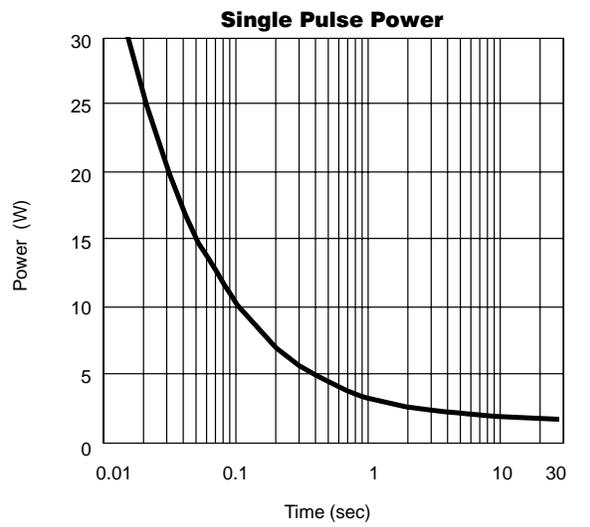
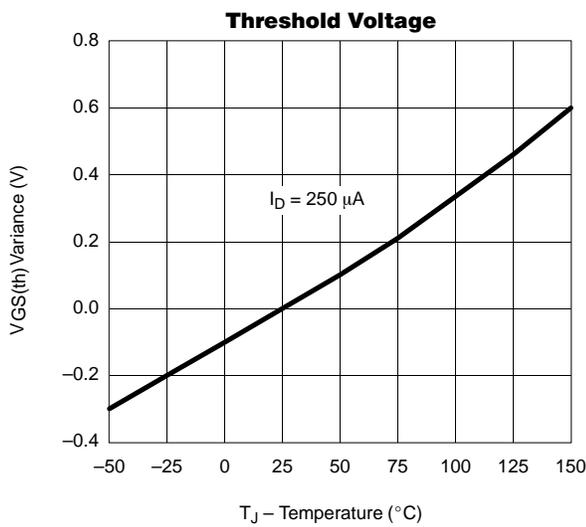
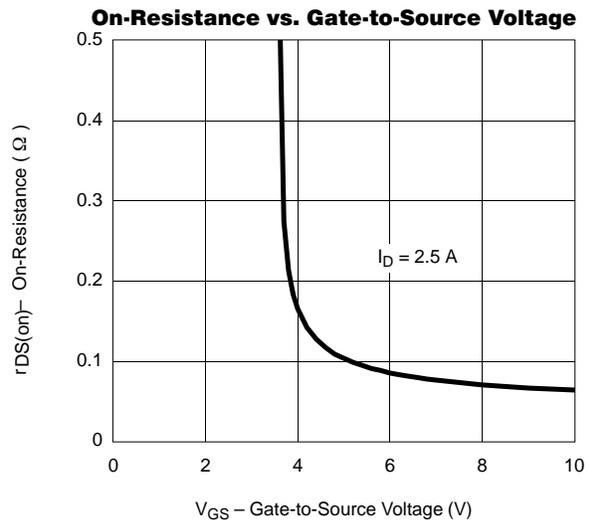
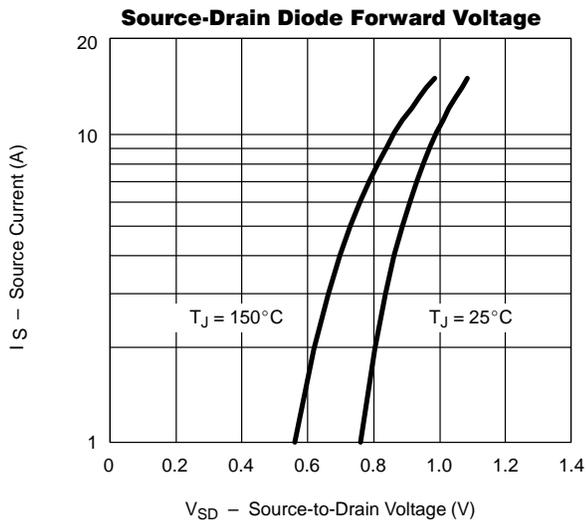
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

P-CHANNEL



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

P-CHANNEL





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